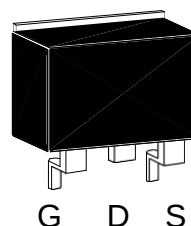


P-Channel Enhancement Mode Power MOSFET

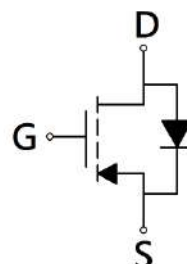
Features:

- Low Gate Charge
- Simple Drive Requirement
- Repetitive Avalanche Rated
- Fast Switching Characteristic
- RoHS compliant package

TO-263



BV_{DSS}	-60V
$I_D @ V_{GS}=-10V, T_C=25^{\circ}C$	-92A
$I_D @ V_{GS}=-10V, T_A=25^{\circ}C$	-12A
$R_{DS(on)(TYP)} @ V_{GS}=-10V, I_D=-10A$	6.7m Ω



G : Gate S : Source D : Drain

Ordering Information

Device	Package	Shipping
KUE5D0P06	TO-263 (Pb-free lead plating and RoHS compliant package)	800 pcs / Tape & Reel

Absolute Maximum Ratings (T_C=25°C, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±30	
Continuous Drain Current @ T _C =25°C, V _{GS} =-10V (Note 4)	I _D	-92	A
Continuous Drain Current @ T _C =100°C, V _{GS} =-10V (Note 4)		-58	
Pulsed Drain Current (Note 3)	I _{DM}	-312	
Continuous Drain Current @ T _A =25°C, V _{GS} =-10V (Note 2)	I _{DSM}	-12	
Continuous Drain Current @ T _A =70°C, V _{GS} =-10V (Note 2)		-9.4	
Avalanche Current @ L=0.1mH (Note 3)	I _{AS}	-32	
Avalanche Energy @ L=1mH	E _{AS}	160	mJ
Power Dissipation	P _D	T _C =25°C (Note 1)	W
		T _C =100°C (Note 1)	
Power Dissipation	P _{DSM}	T _A =25°C (Note 2)	
		T _A =70°C (Note 2)	
Operating Junction and Storage Temperature	T _J , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{θJC}	1	°C/W
Thermal Resistance, Junction-to-ambient, max (Note 2)	R _{θJA}	62	

- Note : 1. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
2. The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
3. Pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.
4. Calculated continuous drain current based on maximum allowable junction temperature.
5. The static characteristics are obtained using <300μs pulses, duty cycle 0.5% maximum.
6. The R_{θJA} is the sum of thermal resistance from junction to case R_{θJC} and case to ambient.

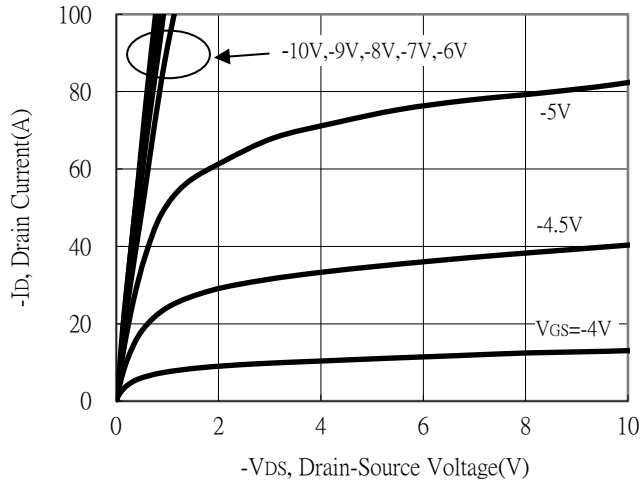
Electrical Characteristics (T_c=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-60	-	-	V	V _{GS} =0V, I _D =-250μA
V _{GS(th)}	-2	-	-4		V _{DS} = V _{GS} , I _D =-250μA
G _{FS}	-	28	-	S	V _{DS} =-10V, I _D =-10A
I _{GSS}	-	-	±100	nA	V _{GS} =±30V, V _{DS} =0V
I _{DSS}	-	-	-1	μA	V _{DS} =-48V, V _{GS} =0V
*R _{DS(ON)}	-	6.7	9	mΩ	V _{GS} =-10V, I _D =-10A
Dynamic					
*Q _g	-	129	-	nC	V _{DS} =-30V, I _D =-10A, V _{GS} =-10V
*Q _{gs}	-	21	-		
*Q _{gd}	-	43	-		
*t _{d(ON)}	-	40	-	ns	V _{DS} =-30V, I _D =-10A, V _{GS} =-10V, R _G =1Ω
*t _r	-	31	-		
*t _{d(OFF)}	-	92	-		
*t _f	-	22	-		
C _{iss}	-	6717	-	pF	V _{DS} =-30V, V _{GS} =0V, f=1MHz
C _{oss}	-	756	-		
C _{rss}	-	347	-		
R _g	-	0.9	-	Ω	f=1MHz
Source-Drain Diode					
*I _S	-	-	-92	A	
*I _{SM}	-	-	-312		
*V _{SD}	-	-0.81	-1.2	V	I _S =-10A, V _{GS} =0V
*t _{rr}	-	32	-	ns	I _F =-10A, V _{GS} =0V, dI _F /dt=100A/μs
*Q _{rr}	-	33	-	nC	

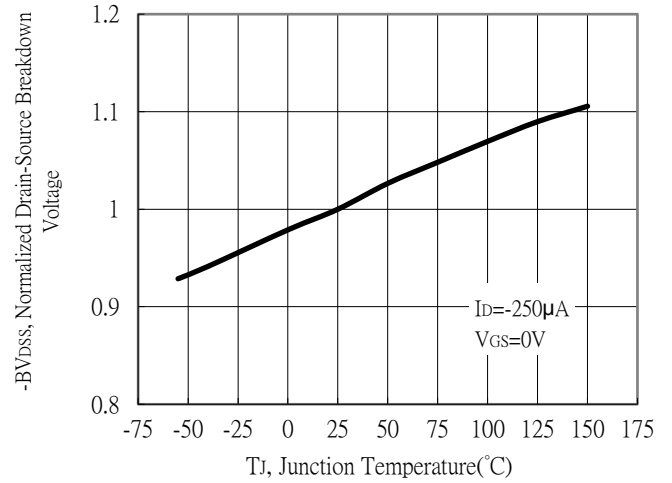
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

Typical Characteristics

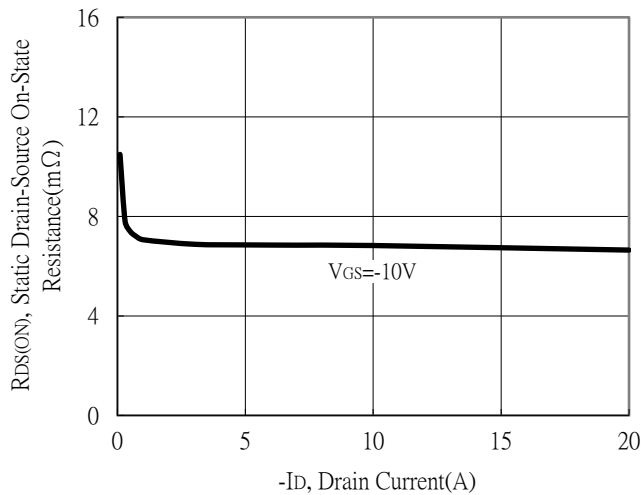
Typical Output Characteristics



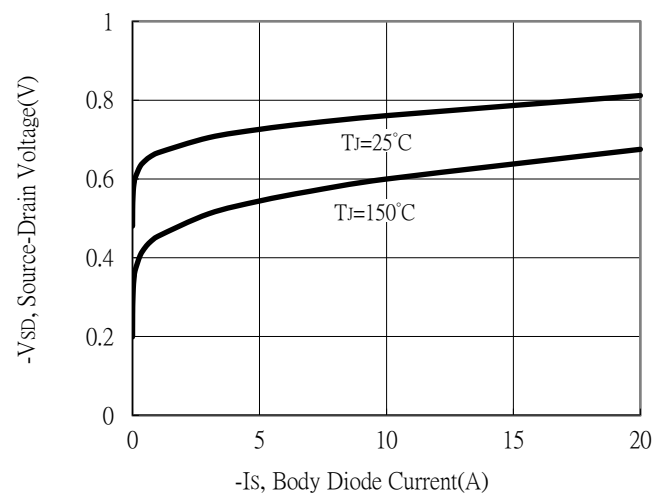
Breakdown Voltage vs Junction Temperature



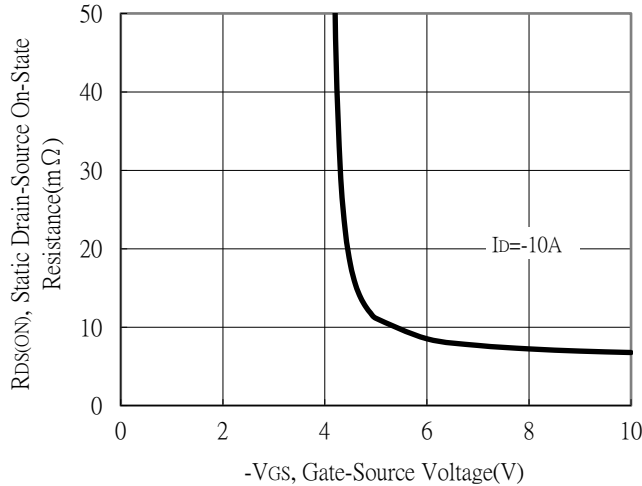
Static Drain-Source On-State resistance vs Drain Current



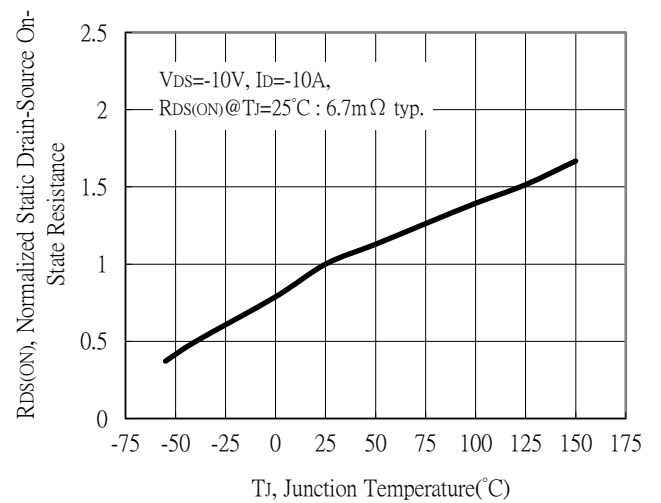
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

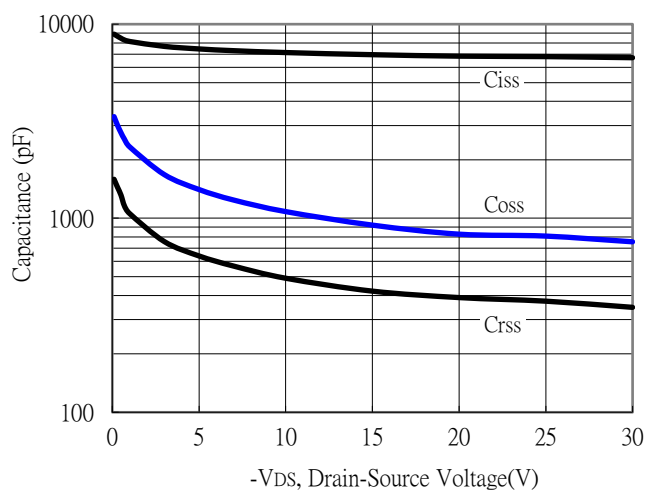


Drain-Source On-State Resistance vs Junction Temperature

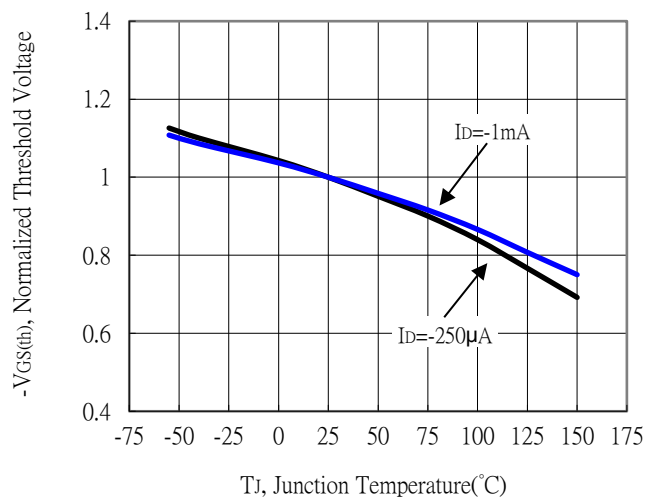


Typical Characteristics (Cont.)

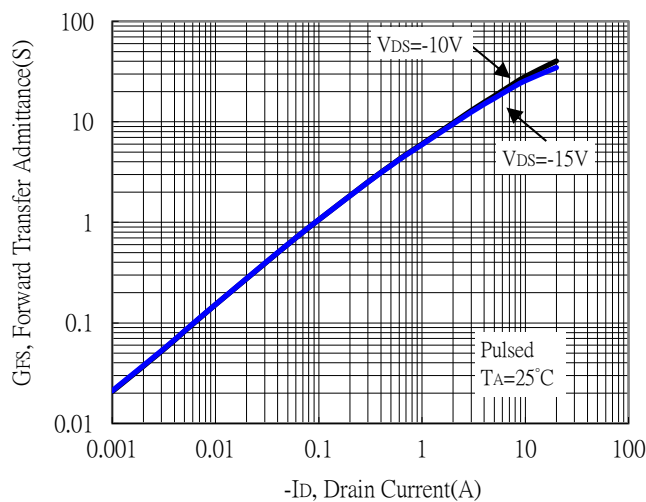
Capacitance vs Drain-to-Source Voltage



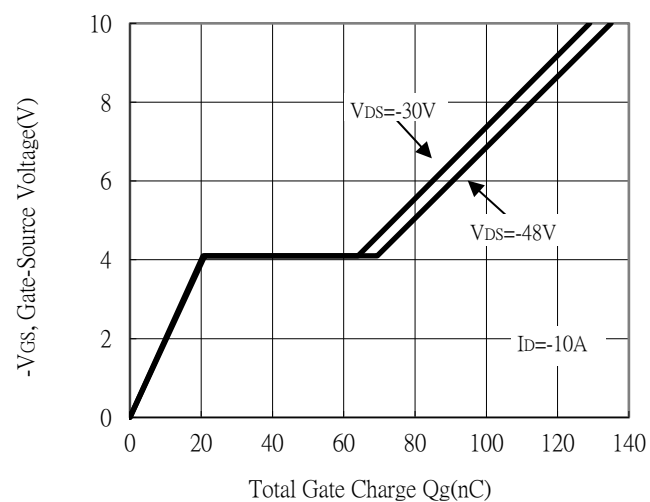
Threshold Voltage vs Junction Temperature



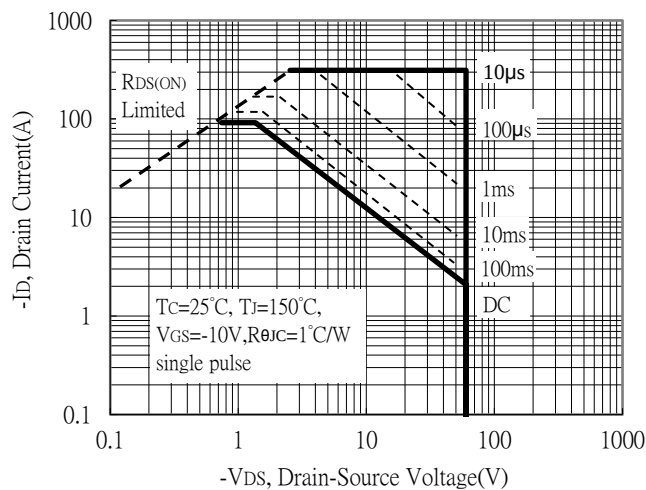
Forward Transfer Admittance vs Drain Current



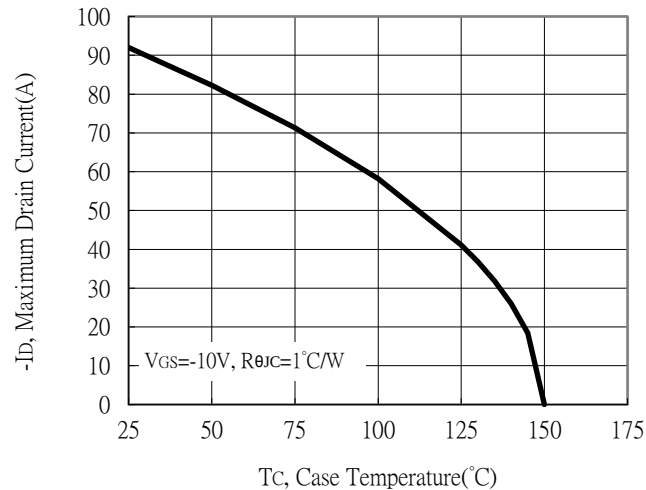
Gate Charge Characteristics



Maximum Safe Operating Area

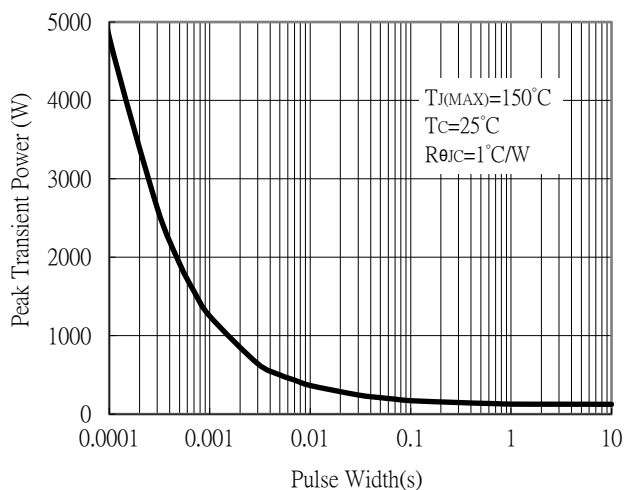


Maximum Drain Current vs Case Temperature

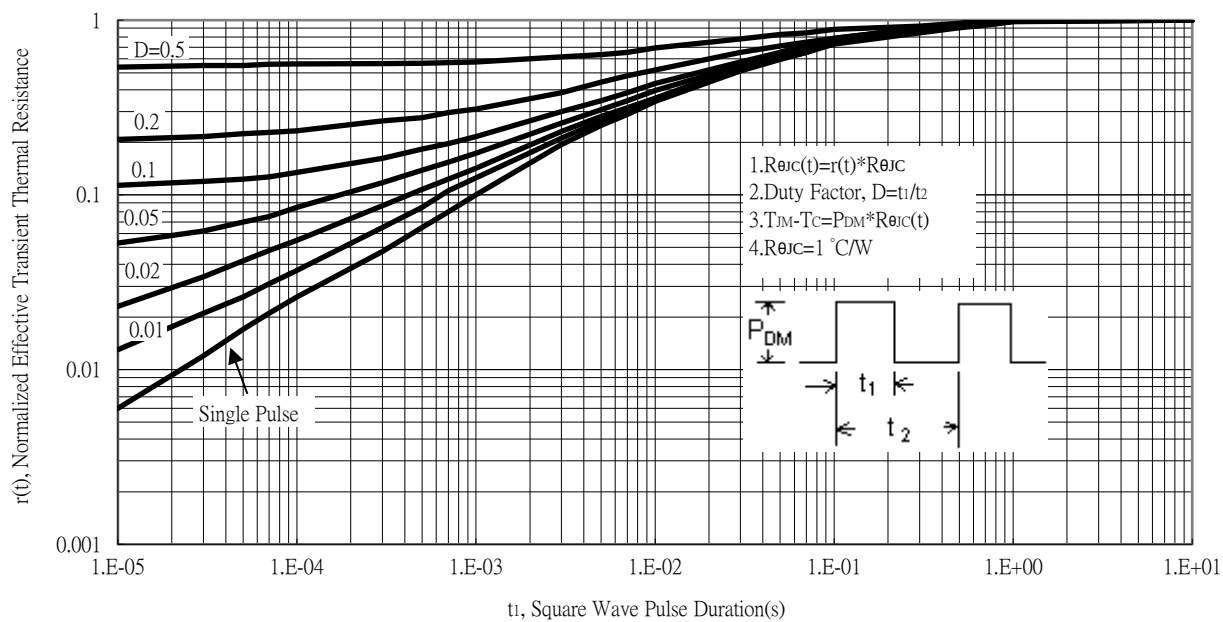


Typical Characteristics (Cont.)

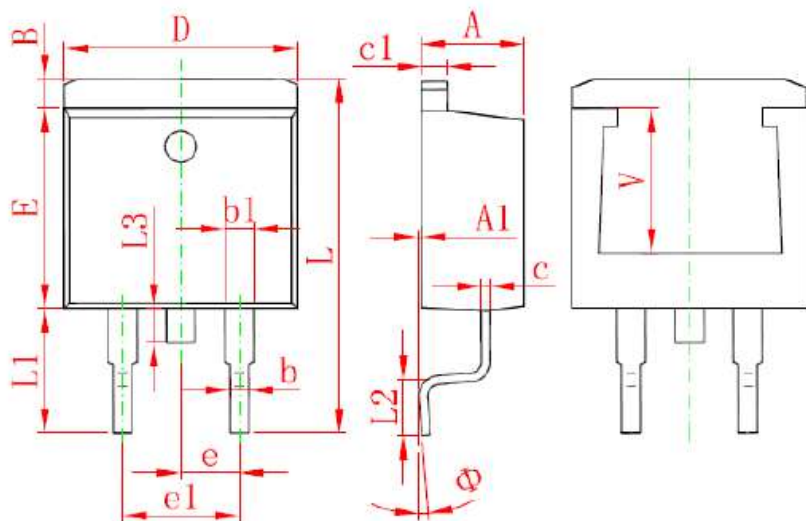
Single Pulse Maximum Power Dissipation



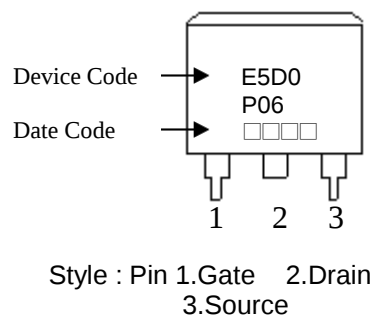
Transient Thermal Response Curves



TO-263 Dimension



Marking :



3-Lead Plastic Surface Mounted Package

Date Code(counting from left to right) :
 1st code: year code, the last digit of Christian year
 2nd code : month code, Jan→A, Feb→B, Mar→C, Apr→D,
 May→E, Jun→F, Jul→G, Aug→H, Sep→J,
 Oct→K, Nov→L, Dec→M
 3rd and 4th codes : production serial number, 01~99

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184	e	2.540 TYP		0.100 TYP	
A1	0.000	0.150	0.000	0.006	e1	4.980	5.180	0.196	0.204
B	1.120	1.420	0.044	0.056	L	14.940	15.500	0.588	0.610
b	0.710	0.910	0.028	0.036	L1	4.950	5.450	0.195	0.215
b1	1.170	1.370	0.046	0.054	L2	2.340	2.740	0.092	0.108
c	0.310	0.530	0.012	0.021	L3	1.300	1.700	0.051	0.067
c1	1.170	1.370	0.046	0.054	Φ	0°	8°	0°	8°
D	10.010	10.310	0.394	0.406	V	6.400 REF		0.253 REF	
E	8.500	8.900	0.335	0.350					